

August 1991

Features

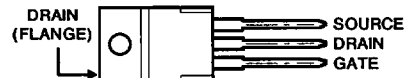
- 2A, 80V and 100V
- $r_{DS(on)} = 1.05\Omega$
- SOA is Power-Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device

Description

The RFP2N08 and RFP2N10 are n-channel enhancement-mode silicon-gate power field-effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

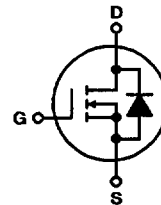
The RFP-types are supplied in the JEDEC TO-220AB plastic package.

Package

 TO-220AB
TOP VIEW


Terminal Diagram

N-CHANNEL ENHANCEMENT MODE



Absolute Maximum Ratings ($T_C = +25^\circ\text{C}$), Unless Otherwise Specified

	RFP2N08	RFP2N10	UNITS
Drain-Source Voltage	80	100	V
Drain-Gate Voltage ($R_{GS} = 1\text{M}\Omega$)	80	100	V
RMS Continuous Drain Current			
$T_C = +25^\circ\text{C}$	2	2	A
Pulsed Drain Current	5	5	A
Gate-to-Source Voltage	± 20	± 20	V
Maximum Power Dissipation			
$T_C = +25^\circ\text{C}$	25	25	W
$T_C > +25^\circ\text{C}$	0.2	0.2	W/ $^\circ\text{C}$
Operating and Storage Junction	-55 to +150	-55 to +150	$^\circ\text{C}$
Temperature Range			

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 N-CHANNEL
POWER MOSFETS

Specifications RFP2N08, RFP2N10

Electrical Characteristics ($T_C = +25^\circ\text{C}$), Unless Otherwise Specified

CHARACTERISTIC	SYMBOLS	TEST CONDITIONS	LIMITS				UNITS
			RFP2N08		RFP2N10		
			MIN	MAX	MIN	MAX	
Drain-Source Breakdown Voltage	V_{DS}	$I_D = 1\text{mA}, V_{GS} = 0$	80	-	100	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2	4	2	4	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 65\text{V}$	-	1	-	-	μA
		$V_{DS} = 80\text{V}$	-	-	-	1	μA
		$T_C = +125^\circ\text{C}$ $V_{DS} = 65\text{V}$	-	50	-	-	μA
		$V_{DS} = 80\text{V}$	-	-	-	50	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0$	-	100	-	100	nA
Drain-Source On-Voltage	$V_{DS(on)}^*$	$I_D = 1\text{A}, V_{GS} = 10\text{V}$	-	1.05	-	1.05	V
		$I_D = 2\text{A}, V_{GS} = 10\text{V}$	-	3.0	-	3.0	V
Static Drain-Source On Resistance	$r_{DS(on)}^*$	$I_D = 1\text{A}, V_{GS} = 10\text{V}$	-	1.05	-	1.05	Ω
Forward Transconductance	g_{fs}^*	$I_D = 1\text{A}, V_{DS} = 10\text{V}$	400	-	400	-	S (f)
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}$ $f = 1\text{MHz}$	-	200	-	200	pF
Output Capacitance	C_{OSS}		-	80	-	80	pF
Reverse Transfer Capacitance	C_{RSS}		-	25	-	25	pF
Turn-On Delay Time	$t_{d(on)}$	$I_D = 1\text{A}, V_{DD} = 50\text{V}$ $R_{GEN} = R_{GS} = 50\Omega$ $V_{GS} = 10\text{V}$	17 (typ)	25	17 (typ)	25	ns
Rise Time	t_r		30 (typ)	45	30 (typ)	45	ns
Turn-Off Delay Time	$t_{d(off)}$		30 (typ)	45	30 (typ)	45	ns
Fall Time	t_f		17 (typ)	25	17 (typ)	25	ns
Thermal Resistance Junction-to-Case	$R_{\theta JC}$		-	5	-	5	$^\circ\text{C/W}$

Source-Drain Diode Ratings and Characteristics

CHARACTERISTIC	SYMBOLS	TEST CONDITIONS	LIMITS				UNITS
			RFP2N08		RFP2N10		
			MIN	MAX	MIN	MAX	
Diode Forward Voltage	V_{SD}^*	$I_{SD} = -1\text{A}$	-	1.4	-	1.4	V
Diode Reverse Recovery Time	t_{rr}	$I_F = 2\text{A}$ $dI_F/dt = 50\text{A}/\mu\text{s}$	100 (typ)	100 (typ)	100 (typ)	100 (typ)	ns

* Pulsed: Pulse duration = 300 μs max., duty cycle = 2%.

RFP2N08, RFP2N10

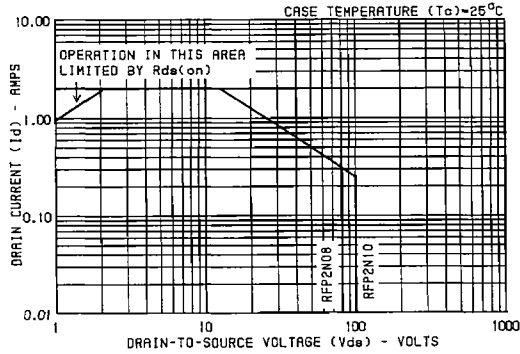


Fig. 1 - Maximum operating areas for all types.

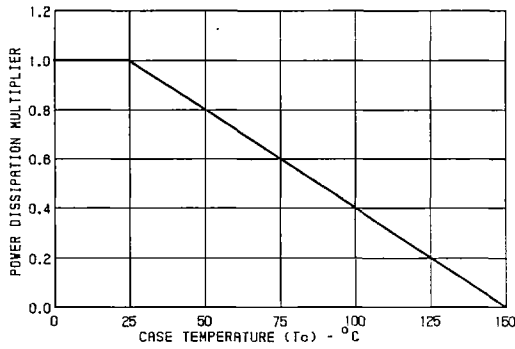


Fig. 2 - Normalized power dissipation vs. temperature derating curve

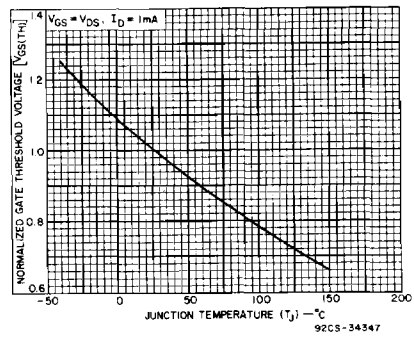


Fig. 3 - Typical normalized gate threshold voltage as a function of junction temperature for all types.

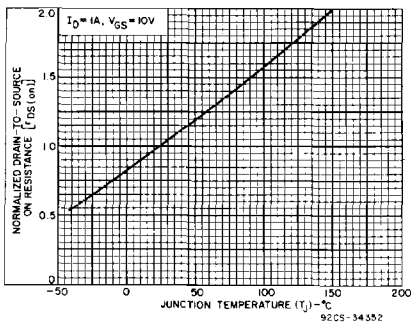


Fig. 4 - Normalized drain-to-source on resistance to junction temperature for all types.

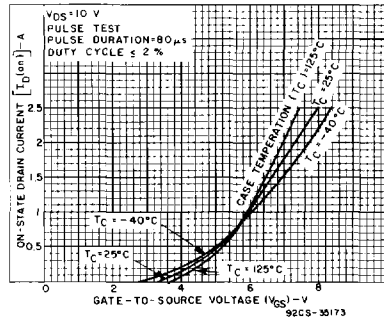


Fig. 5 - Typical transfer characteristics for all types.

RFP2N08, RFP2N10

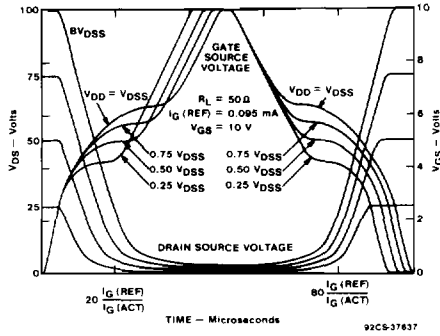


Fig. 6 - Normalized switching waveforms for constant gate-current. Refer to Harris application notes AN-7254 and AN-7260.

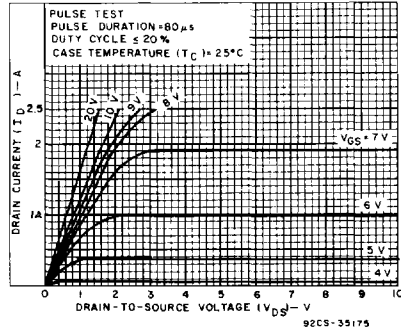


Fig. 7 - Typical saturation characteristics for all types.

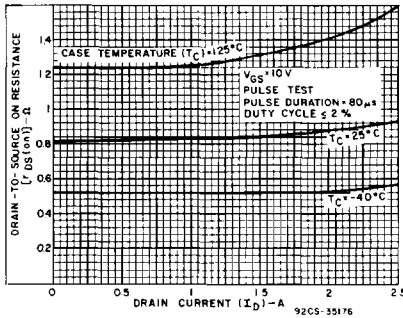


Fig. 8 - Typical drain-to-source on resistance as a function of drain current for all types.

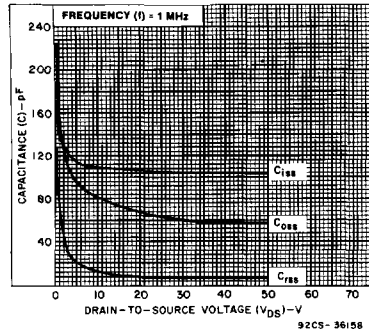


Fig. 9 - Capacitance as a function of drain-to-source voltage for all types.

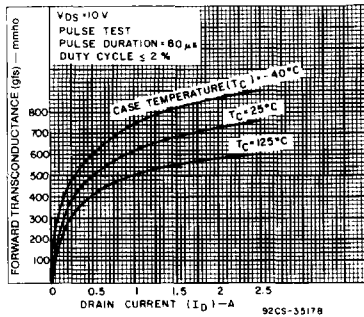


Fig. 10 - Typical forward transconductance as a function of drain current for all types.

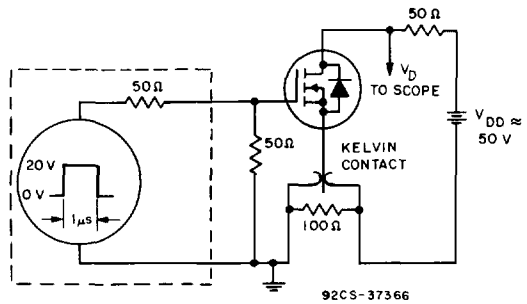


Fig. 11 - Switching Time Test Circuit.